



# Bipolar PNP Bare Die – BTP6031

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## Part Description

The BTP6031 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

## Key Parameters:

- VCBO = -15V
- VCEO = -12V
- VEBO = -6V
- hFE = 270-680 @ VCE = -2V, IC = -0.01A
- VCE(Sat) = -0.25V @ IC = -0.2A, IB = -10mA
- fT = 260 MHz @ VCE = -2V, IE = 0A
- COBO = 6pF @ VCB = -10V

## Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SA2030

## Die Size (Unsawn)

400µm X 400µm, 16 Mils X 16 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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